

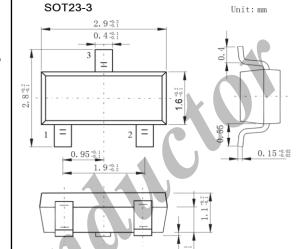
# **60V N-Channel Enhancement Mode MOSFET**

#### • General Description

APLML0060B combines advanced MOSFET technology with a low resistance package to provide extremely low  $R_{DS(\text{ON})}$ . This device is most suitable to load switch or PWM applications.

# G 1 3 D

Top View



#### Applications

- Load / System Switch

#### Product Summary

$V_{\mathrm{DS}}$	60V
$I_D$ (at $V_{GS} = 10V$ )	3.7A
$R_{DS(ON)}$ (at $V_{GS} = 10V$ )	< 100mΩ
$R_{DS(ON)}$ (at $V_{GS} = 4.5V$ )	< 120mΩ



## Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit			
Drain-Source Voltage	$V_{DS}$	60	V			
Gate-Source Voltage	$V_{GS}$	±20	V			
Continuous Drain Current	$I_D$	3.7	۸			
Pulsed Drain Current	$I_{DM}$	25	A			
Power Dissipation	$P_D$	1.4	W			
Thermal Characteristics						
Junction and Storage Temperature Range	$T_J$ , $T_{STG}$	-55 to 150	°C			
Thermal Resistance. Junction-to-Ambient	$R_{ heta JA}$	55	°C/W			



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#### • Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static Parameters						
Drain-Source Breakdown Voltage	$V_{DSS}$	I <sub>D</sub> =250Aμ, V <sub>GS</sub> =0V	60			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}$ =60V, $V_{GS}$ =0V			1	μΑ
Gate-Source Leakage Current	$I_{GSS}$	$V_{DS}$ =0V, $V_{GS}$ =±20V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	1		3	V
On-State Drain Current	I <sub>D(ON)</sub>	$V_{GS}$ =5V , $V_{DS}$ =10V	8			Α
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =3.9A			100	mΩ
	IVDS(UN)	V <sub>GS</sub> =4.5V, I <sub>D</sub> =3.7A	AB		120	
Forward Transconductance	$\mathbf{g}_{ extsf{FS}}$	$V_{DS}$ =5V, $I_D$ =3.7A	3	9		S
Diode Forward Voltage	$V_{\text{SD}}$	$I_S=1.5A$ , $V_{GS}=0V$	7		1.2	V
Maximum Body-Diode Continuous Current	Is				2.5	Α
Dynamic Parameters						
Input Capacitance	$C_{iss}$				800	
Output Capacitance	$C_{oss}$	$V_{GS}$ =0V, $V_{DS}$ =25V, f=1MHz			250	pF
Reverse Transfer Capacitance	$C_{rss}$				60	
Switching Parameters						
Total Gate Charge	Qg			9	12	
Gate Source Charge	$Q_{\mathrm{gs}}$	$V_{GS}$ =10V, $V_{DS}$ =40V, $I_{D}$ =3.7A		2		nC
Gate Drain Charge	$Q_{\mathrm{gd}}$			6		1 1
Turn-On Delay Time	$t_{D(on)}$			15	20	
Turn-On Rise Time	$t_{\rm r}$	I _1		18	20	na
Turn-Off Delay Time	$t_{\mathrm{D(off)}}$	$I_D=1A$ , $V_{DS}=25V$ , $R_{GEN}=6\Omega$		40	50	ns
Turn-Off Fall Time	$t_{\rm f}$			16	20	

#### • Ordering Information

Ordering Part Number	Package	MOQ
APLML0060B	SOT23-3	3,000 pcs / reel

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## **60V N-Channel Enhancement Mode MOSFET**

#### • Typical Electrical and Thermal Characteristics

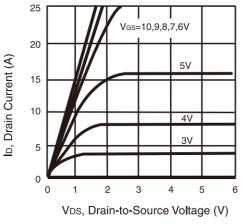
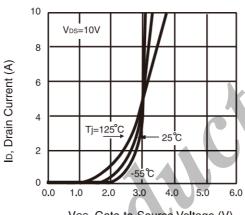


Figure 1. Output Characteristics



Vgs, Gate-to-Source Voltage (V)

Figure 2. Transfer Characteristics

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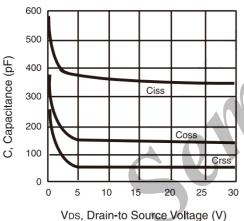


Figure 3. Capacitance

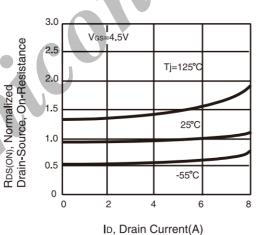


Figure 4. On-Resistance Variation with Drain Current and Temperature

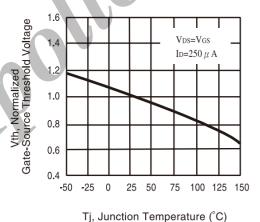
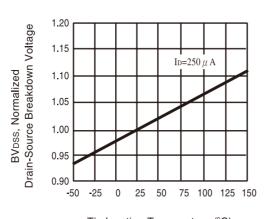


Figure 5. Gate Threshold Variation with Temperature



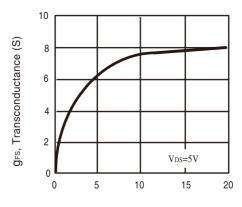
Tj, Junction Temperature (°C)

Figure 6. Breakdown Voltage Variation with Temperature



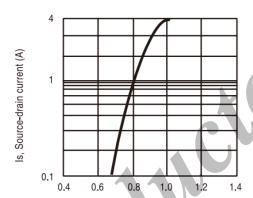
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#### • Typical Electrical and Thermal Characteristics



IDS, Drain-Source Current (A)

Figure 7. Transconductance Variation with Drain Current



Vsp, Body Diode Forward Voltage (V)

Figure 8. Body Diode Forward Voltage Variation with Source Current

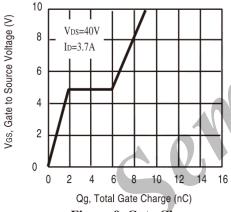


Figure 9. Gate Charge

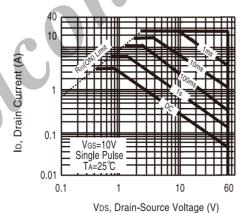
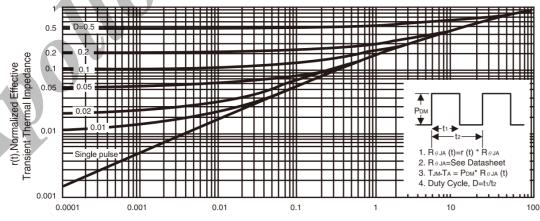


Figure 10. Maximum Safe Operating Area



Square Wave Pulse Duration (sec)

Figure 11. Normalized Thermal Transient Impedance Curve



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